5 Watt Surmetic40 Zener Voltage Regulators

1N53 Series

This is a complete series of 5 Watt Zener diodes with tight limits and better operating characteristics that reflect the superior capabilities of silicon–oxide passivated junctions. All this in an axial lead, transfer–molded plastic package that offers protection in all common environmental conditions.

Features

- Zener Voltage Range 3.3 V to 200 V
- ESD Rating of Class 3 (>16 kV) per Human Body Model
- Surge Rating of up to 180 W @ 8.3 ms
- Maximum Limits Guaranteed on up to Six Electrical Parameters
- Pb-Free Packages are Available*

Mechanical Characteristics

CASE: Void free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are

readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:

260°C, 1/16 in. from the case for 10 seconds **POLARITY:** Cathode indicated by polarity band

MOUNTING POSITION: Any

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ T _L = 25°C, Lead Length = 3/8 in	P_{D}	5	W
Derate above 25°C		40	mW/°C
Junction-to-Lead Thermal Resistance	$\theta_{\sf JL}$	25	°C/W
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +200 (Note 1)	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

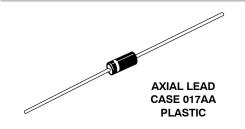
1. Max operating temperature for DC conditions is 150°C, but not to exceed 200°C for pulsed conditions with low duty cycle or non-repetitive.



ON Semiconductor®

www.onsemi.com





MARKING DIAGRAM



A = Assembly Location 1N53xxB = Device Number

(Refer to Tables on Pages 3 & 4)

YY = Year WW = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

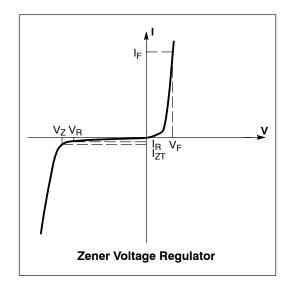
Device	Package	Shipping [†]
1N53xxB, G	Axial Lead (Pb-Free)	1000 Units/Box
1N53xxBRL, G	Axial Lead (Pb-Free)	4000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 1.2 \text{ V Max}$ @ $I_F = 1.0 \text{ A for all types}$)

Symbol	Parameter
Vz	Reverse Zener Voltage @ I _{ZT}
I _{ZT}	Reverse Current
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}
I _{ZK}	Reverse Current
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}
I _R	Reverse Leakage Current @ V _R
V _R	Breakdown Voltage
I _F	Forward Current
V _F	Forward Voltage @ I _F
I _R	Maximum Surge Current @ T _A = 25°C
ΔV_Z	Reverse Zener Voltage Change
I _{ZM}	Maximum DC Zener Current



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, V_F = 1.2 V Max @ I_F = 1.0 A for all types)

	Zener Voltage (Note 3)		Zener Voltage (Note 3) Zener Impedance (Note 3		Zener Voltage (Note 3)			te 3)	Leakage Current		I _R	ΔV _Z	I _{ZM}
Device [†]	Device	V	z (Volts	s)	@ I _{ZT}	Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK}	I _{ZK}	I _R @ '	V _R	(Note 4)	(Note 5)	(Note 6)
(Note 2)	Marking	Min	Nom	Max	mA	Ω	Ω	mA	μ Α Max	Volts	Α	Volts	mA
1N5333B	1N5333B	3.14	3.3	3.47	380	3	400	1	300	1	20	0.85	1440
1N5334B	1N5334B	3.42	3.6	3.78	350	2.5	500	1	150	1	18.7	0.8	1320
1N5335B	1N5335B	3.71	3.9	4.10	320	2	500	1	50	1	17.6	0.54	1220
1N5336B	1N5336B	4.09	4.3	4.52	290	2	500	1	10	1	16.4	0.49	1100
1N5337B	1N5337B	4.47	4.7	4.94	260	2	450	1	5	1	15.3	0.44	1010
1N5338B	1N5338B	4.85	5.1	5.36	240	1.5	400	1	1	1	14.4	0.39	930
1N5339B	1N5339B	5.32	5.6	5.88	220	1	400	1	1	2	13.4	0.25	865
1N5340B	1N5340B	5.70	6.0	6.30	200	1	300	1	1	3	12.7	0.19	790
1N5341B	1N5341B	5.89	6.2	6.51	200	1	200	1	1	3	12.4	0.1	765
1N5342B	1N5342B	6.46	6.8	7.14	175	1	200	1	10	5.2	11.5	0.15	700
1N5343B	1N5343B	7.13	7.5	7.88	175	1.5	200	1	10	5.7	10.7	0.15	630
1N5344B	1N5344B	7.79	8.2	8.61	150	1.5	200	1	10	6.2	10	0.2	580
1N5345B	1N5345B	8.27	8.7	9.14	150	2	200	1	10	6.6	9.5	0.2	545
1N5346B	1N5346B	8.65	9.1	9.56	150	2	150	1	7.5	6.9	9.2	0.22	520
1N5347B	1N5347B	9.50	10	10.5	125	2	125	1	5	7.6	8.6	0.22	475

Devices listed in bold, italic are ON Semiconductor Preferred devices. Preferred devices are recommended choices for future use and best overall value.

- 2. TOLERANCE AND TYPE NUMBER DESIGNATION: The JEDEC type numbers shown indicate a tolerance of ±5%.
- ZENER VOLTAGE (V_Z) and IMPEDANCE (I_{ZT} and I_{ZK}): Test conditions for zener voltage and impedance are as follows: I_Z is applied 40 ±10 ms prior to reading. Mounting contacts are located 3/8" to 1/2" from the inside edge of mounting clips to the body of the diode (T_A = 25°C +8°C, -2°C).
- 4. SURGE CURRENT (I_R): Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a pulse width, PW, of 8.3 ms. The data given in Figure 5 may be used to find the maximum surge current for a square wave of any pulse width between 1 ms and 1000 ms by plotting the applicable points on logarithmic paper. Examples of this, using the 3.3 V and 200 V zener are shown in Figure 6. Mounting contact located as specified in Note 2 (T_A = 25°C +8°C, -2°C).
- VOLTAGE REGULATION (ΔV_Z): The conditions for voltage regulation are as follows: V_Z measurements are made at 10% and then at 50% of the I_Z max value listed in the electrical characteristics table. The test current time duration for each V_Z measurement is 40 ±10 ms. Mounting contact located as specified in Note 2 (T_A = 25°C +8°C, -2°C).
- 6. MAXIMUM REGULATOR CURRENT (I_{ZM}): The maximum current shown is based on the maximum voltage of a 5% type unit, therefore, it applies only to the B-suffix device. The actual I_{ZM} for any device may not exceed the value of 5 watts divided by the actual V_Z of the device. T_L = 25°C at 3/8" maximum from the device body.

†The "G" suffix indicates Pb-Free package or Pb-Free packages are available.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, V_F = 1.2 V Max @ I_F = 1.0 A for all types)

		Zen	er Volta	age (Not	e 8)	Zener Impedance (Note 8)			Leakage Current		ΔV _Z	ΔV _Z (Note	I _{ZM}
Device [†]	Device	V	z (Volts	s)	@ I _{ZT}	Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK}	I _{ZK}	I _R @	V _R	(Note 9)	10)	(Note 11)
(Note 7)	Marking	Min	Nom	Max	mA	Ω	Ω	mA	μ Α Max	Volts	Α	Volts	mA
1N5348B	1N5348B	10.45	11	11.55	125	2.5	125	1	5	8.4	8.0	0.25	430
1N5349B	1N5349B	11.4	12	12.6	100	2.5	125	1	2	9.1	7.5	0.25	395
1N5350B	1N5350B	12.35	13	13.65	100	2.5	100	1	1	9.9	7.0	0.25	365
1N5351B	1N5351B	13.3	14	14.7	100	2.5	75	1	1	10.6	6.7	0.25	340
1N5352B	1N5352B	14.25	15	15.75	<i>75</i>	2.5	<i>75</i>	1	1	11.5	6.3	0.25	315
1N5353B	1N5353B	15.2	16	16.8	<i>75</i>	2.5	<i>75</i>	1	1	12.2	6.0	0.3	295
1N5354B	1N5354B	16.15	17	17.85	70	2.5	75	1	0.5	12.9	5.8	0.35	280
1N5355B	1N5355B	17.1	18	18.9	65	2.5	75	1	0.5	13.7	5.5	0.4	264
1N5356B	1N5356B	18.05	19	19.95	65	3	75	1	0.5	14.4	5.3	0.4	250
1N5357B	1N5357B	19	20	21	65	3	75	1	0.5	15.2	5.1	0.4	237
1N5358B	1N5358B	20.9	22	23.1	50	3.5	<i>75</i>	1	0.5	16.7	4.7	0.45	216
1N5359B	1N5359B	22.8	24	25.2	50	3.5	100	1	0.5	18.2	4.4	0.55	198
1N5360B	1N5360B	23.75	25	26.25	50	4	110	1	0.5	19	4.3	0.55	190
1N5361B	1N5361B	25.65	27	28.35	50	5	120	1	0.5	20.6	4.1	0.6	176
1N5362B	1N5362B	26.6	28	29.4	50	6	130	1	0.5	21.2	3.9	0.6	170
1N5363B	1N5363B	28.5	30	31.5	40	8	140	1	0.5	22.8	3.7	0.6	158
1N5364B	1N5364B	31.35	33	34.65	40	10	150	1	0.5	25.1	3.5	0.6	144
1N5365B	1N5365B	34.2	36	37.8	30	11	160	1	0.5	27.4	3.5	0.65	132
1N5366B	1N5366B	37.05	39	40.95	30	14	170	1	0.5	29.7	3.1	0.65	122
1N5367B	1N5367B	40.85	43	45.15	30	20	190	1	0.5	32.7	2.8	0.7	110
1N5368B	1N5368B	44.65	47	49.35	25	25	210	1	0.5	35.8	2.7	0.8	100
1N5369B	1N5369B	48.45	51	53.55	25	27	230	1	0.5	38.8	2.5	0.9	93
1N5370B	1N5370B	53.2	56	58.8	20	35	280	1	0.5	42.6	2.3	1.0	86
1N5371B	1N5371B	57	60	63	20	40	350	1	0.5	45.5	2.2	1.2	79
1N5372B	1N5372B	58.9	62	65.1	20	42	400	1	0.5	47.1	2.1	1.35	76
1N5373B	1N5373B	64.6	68	71.4	20	44	500	1	0.5	51.7	2.0	1.52	70
1N5374B	1N5374B	71.25	75	78.75	20	45	620	1	0.5	56	1.9	1.6	63
1N5375B	1N5375B	77.9	82	86.1	15	65	720	1	0.5	62.2	1.8	1.8	58
1N5377B	1N5377B	86.45	91	95.55	15	75	760	1	0.5	69.2	1.6	2.2	52.5
1N5378B	1N5378B	95	100	105	12	90	800	1	0.5	76	1.5	2.5	47.5
1N5380B	1N5380B	114	120	126	10	170	1150	1	0.5	91.2	1.3	2.5	39.5
1N5381B	1N5381B	123.5	130	136.5	10	190	1250	1	0.5	98.8	1.2	2.5	36.6
1N5383B	1N5383B	142.5	150	157.5	8	330	1500	1	0.5	114	1.1	3.0	31.6
1N5384B	1N5384B	152	160	168	8	350	1650	1	0.5	122	1.1	3.0	29.4
1N5386B	1N5386B	171	180	189	5	430	1750	1	0.5	137	1.0	4.0	26.4
1N5387B	1N5387B	180.5	190	199.5	5	450	1850	1	0.5	144	0.9	5.0	25
1N5388B	1N5388B	190	200	210	5	480	1850	1	0.5	152	0.9	5.0	23.6

Devices listed in bold, italic are ON Semiconductor Preferred devices. Preferred devices are recommended choices for future use and best overall value.

- 7. **TOLERANCE AND TYPE NUMBER DESIGNATION:** The JEDEC type numbers shown indicate a tolerance of $\pm 5\%$.
- 8. **ZENER VOLTAGE (V_Z) and IMPEDANCE (I_{ZT} and I_{ZK}):** Test conditions for zener voltage and impedance are as follows: I_Z is applied 40 ±10 ms prior to reading. Mounting contacts are located 3/8" to 1/2" from the inside edge of mounting clips to the body of the diode (T_A = 25°C +8°C, -2°C).
- 9. **SURGE CURRENT** (I_R): Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a pulse width, PW, of 8.3 ms. The data given in Figure 5 may be used to find the maximum surge current for a square wave of any pulse width between 1 ms and 1000 ms by plotting the applicable points on logarithmic paper. Examples of this, using the 3.3 V and 200 V zener are shown in Figure 6. Mounting contact located as specified in Note 7 (T_A = 25°C +8°C, -2°C).
- 10. VOLTAGE REGULATION (ΔV_Z): The conditions for voltage regulation are as follows: V_Z measurements are made at 10% and then at 50% of the I_Z max value listed in the electrical characteristics table. The test current time duration for each V_Z measurement is 40 ±10 ms. Mounting contact located as specified in Note 7 ($T_A = 25^{\circ}\text{C} + 8^{\circ}\text{C}, -2^{\circ}\text{C}$).
- 11. MAXIMUM REGULATOR CURRENT (I_{ZM}): The maximum current shown is based on the maximum voltage of a 5% type unit, therefore, it applies only to the B-suffix device. The actual I_{ZM} for any device may not exceed the value of 5 watts divided by the actual V_Z of the device. $T_L = 25^{\circ}\text{C}$ at 3/8" maximum from the device body.

†The "G" suffix indicates Pb-Free package or Pb-Free packages are available.

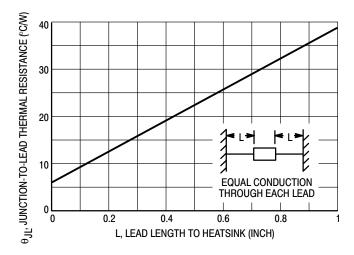


Figure 1. Typical Thermal Resistance

TEMPERATURE COEFFICIENTS

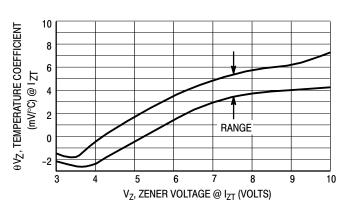


Figure 2. Temperature Coefficient-Range for Units 3 to 10 Volts

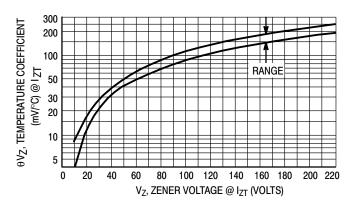


Figure 3. Temperature Coefficient-Range for Units 10 to 220 Volts

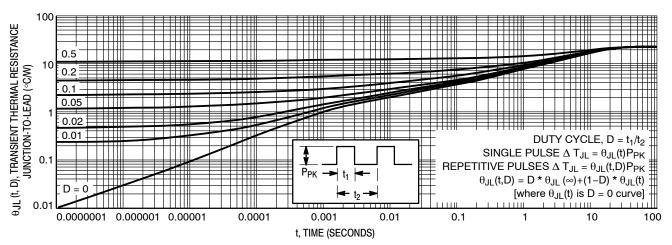


Figure 4. Typical Thermal Response L, Lead Length = 3/8 Inch

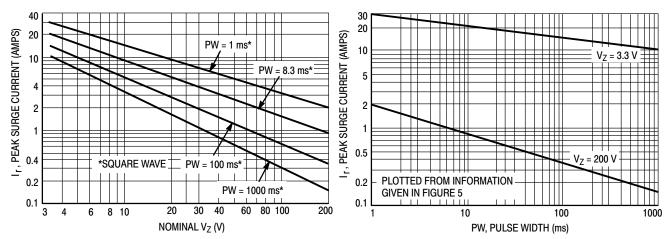


Figure 5. Maximum Non-Repetitive Surge Current versus Nominal Zener Voltage (See Note 4)

Figure 6. Peak Surge Current versus Pulse Width (See Note 4)

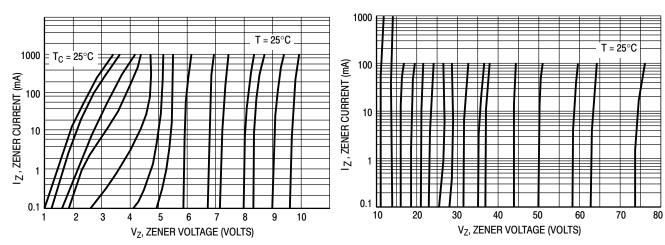


Figure 7. Zener Voltage versus Zener Current $V_Z = 3.3 \text{ thru } 10 \text{ Volts}$

Figure 8. Zener Voltage versus Zener Current $V_Z = 11 \ thru \ 75 \ Volts$

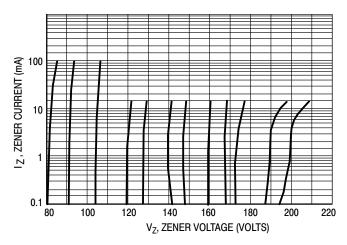


Figure 9. Zener Voltage versus Zener Current V_Z = 82 thru 200 Volts

APPLICATION NOTE

Since the actual voltage available from a given Zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA} P_D + T_A$$

 θ_{LA} is the lead-to-ambient thermal resistance and P_D is the power dissipation.

Junction Temperature, T_J, may be found from:

$$T_J = T_L + \Delta T_{JL}$$

 ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 4 for a train of power pulses or from Figure 1 for dc power.

$$\Delta T_{JL} = \theta_{JL} \; P_D$$

For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of T_J (ΔT_J) may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta V = \theta_{VZ} \, \Delta T_J$$

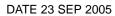
 $\theta_{VZ}\!,$ the Zener voltage temperature coefficient, is found from Figures 2 and 3.

Under high power-pulse operation, the Zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

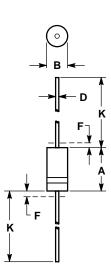
Data of Figure 4 should not be used to compute surge capability. Surge limitations are given in Figure 5. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 5 be exceeded.

SURMETIC 40, AXIAL LEAD CASE 017AA-01

ISSUE O







- NOTES:
 1. CONTROLLING DIMENSION: INCH
 2. LEAD DIAMETER AND FINISH NOT CONTROLLED WITHIN DIMENSION F.
 3. CATHODE BAND INDICATES POLARITY

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.330	0.350	8.38	8.89
В	0.130	0.145	3.30	3.68
D	0.037	0.043	0.94	1.09
F		0.050		1.27
K	1.000	1.250	25.40	31.75

DOCUMENT NUMBER:	98AON21393D	Electronic versions are uncontrolle	•	
STATUS:	ON SEMICONDUCTOR STANDARD	accessed directly from the Document versions are uncontrolled except	' '	
NEW STANDARD:		"CONTROLLED COPY" in red.		
DESCRIPTION:	SURMETIC 40, AXIAL LEAD		PAGE 1 OF 2	

ON Semiconductor®	0
-------------------	---

DOCUMENT NUMBER: 98AON21393D

PAGE 2 OF 2

ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION. REQ. BY M. LYALL.	23 SEP 2005
_		

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: a Phone: 00421 33 790 2910

Phone: 011 421 33 790 2910 For additional information, please contact your local Sales Representative